

**Amendment to the Claims:**

This listing of claims will replace all prior versions and listings of claims in the application:

**Listing of Claims:**

1. (original) A pre-packaged component device comprising:
  - a first non-conductive substrate member having an outer surface;
  - a second non-conductive substrate member having an outer surface;
  - a first layer of solderable electrically conductive material secured to the outer surface of said first non-conductive substrate member;
  - a second layer of solderable electrically conductive material secured to the outer surface of said second non-conductive substrate member;
  - and
  - lead members and a transistor member positioned between said first and second non-conductive substrate members, said transistor having at least one gate.
2. (original) The component device as recited in claim 1 wherein said first and second non-conductive substrate members are made from a ceramic material.
3. (original) The component device as recited in claim 2 wherein said ceramic material is taken from the group consisting of alumina, aluminum nitride, silicon nitride, and beryllium oxide.
4. (withdrawn) The component device as recited in claim 1 wherein said solderable electrically conductive material is a copper material and is direct bonded to said first and second substrate members.

5. (original) The component device as recited in claim 1 wherein said lead members comprise a gate pin, a drain member and a source member.

6. (original) The component device as recited in claim 5 wherein said lead members are stamped from a copper material during manufacture.

7. (withdrawn) The component device as recited in claim 1 further comprising a drain pad positioned on the inside surface of said first nonconductive substrate member and a source pad and gate runner positioned on the inside surface of said second non-conductive substrate member.

8. (currently amended) The component device as recited in claim 1 wherein said transistor member is a metal oxide semiconductor field effect transistor (MOSFET) ~~MOSFET~~.

9. (withdrawn, currently amended) The component device as recited in claim 1 wherein said transistor member is an isolated gate bipolar transistor (IGBT) ~~IGBT~~.

10. (cancelled)

11. (cancelled)

12. (cancelled)

13. (cancelled)

14. (New) The component device as recited in claim 1 wherein said lead members comprise a gate pin, a plurality of drain members and a plurality of source members.